

^{196}At α decay 1996En01,2000Sm06,2005De01

Type	Author	History
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		NDS 113, 1871 (2012)
		15-Jun-2012

Parent: ^{196}At : E=0.0; $J^\pi=(3^+)$; $T_{1/2}=387$ ms *14*; $Q(\alpha)=7198$ 50; % α decay=94 5

$^{196}\text{At}-J^\pi$: Probable configuration is $(\pi h_{9/2})(\nu 3p_{3/2})$ coupled to give $J=3$, analogous to neighboring odd-odd nuclides, e.g., ^{198}At and ^{196}Bi ([2000Sm06](#)).

$^{196}\text{At}-T_{1/2}$: Weighted average of 389 ms *54* ([2005De01](#)), 388 ms *7* ([2000Sm06](#)) and 300 ms *100* ([1967Tr06](#)). others: 390 ms +270–120 ([1996En01](#)), 320 ms +220–90 ([1995Mo14](#)), 253 ms *9* ([1997Pu01](#)). the latter datum is inconsistent with data from [2005De01](#), [2000Sm06](#) and [1996En01](#); the reason for this discrepancy is not known.

$^{196}\text{At}-\% \alpha$ decay: From ^{200}Fr mother/daughter α intensities ([2005De01](#)). Consistent with calculated partial $T_{1/2}$ for β decay of ≈ 5 s from gross β decay theory ([1973Ta30](#)) or 5.2 s ([1997Mo25](#)); the latter implies $\%\varepsilon+\beta^+ \approx 7.4$ assuming $T_{1/2}=387$ ms *14* for ^{196}At .

Others: [1967Tr06](#), [1995Mo14](#), [1997Pu01](#).

[2005De01](#): ^{196}At from α decay of ^{200}Fr ; Si detector (FWHM=30 keV); measured $E\alpha$, parent $T_{1/2}$, branching. see also [2004DeZV](#).

[2000Sm06](#): ^{196}At from $^{165}\text{Ho}(^{36}\text{Ar},5n)$ At E=178 MeV; RITU gas-filled separator; 16-strip position-sensitive Si detector; measured $E\alpha$, parent $T_{1/2}$.

[1997Pu01](#): ^{196}At from $^{166}\text{Er}(^{36}\text{Ar},P5N)$ using 208 MeV pulsed beam; 96.3% enriched ^{166}Er target; GARIS gas-filled recoil separator with position-sensitive detector At focal plane; measured $E\alpha$, (evaporation residue)- $\alpha 1-\alpha 2$ correlations.

[1967Tr06](#): sources from $^{185}\text{Re}(^{20}\text{Ne},9n)$, $^{187}\text{Re}(^{20}\text{Ne},11n)$ (E(^{20}Ne)=100-200 MeV, helium-jet transport); 96.66% ^{185}Re and 96.7% ^{187}Re targets; measured $E\alpha$, parent $T_{1/2}$ (silicon surface-barrier detectors).

 ^{192}Bi Levels

E(level)	J^π [†]
0.0	(3 ⁺)

[†] From Adopted Levels.

 α radiations

$E\alpha$	E(level)	$I\alpha$ [‡]	HF [†]	Comments
7049 3	0.0	100	4.0 7	Decay to low-spin isomer assumed. $E\alpha$: weighted average of 7055 7 (1967Tr06), 7044 7 (1996En01), 7048 5 (2000Sm06) and 7055 12 (2005De01); this $E\alpha$ implies $Q(\alpha)=7196$ 3 if this is a g.s. to g.s. transition, cf. $Q(\alpha)=7198$ 50 from 2011AuZZ . Other $E\alpha$: 7053 30 (1995Mo14), 7065 30 (1997Pu01).

[†] For $r_0=1.540$ *18* (unweighted average of $r_0(^{192}\text{Pb})=1.513$ 3 and $r_0(^{192}\text{Po})=1.585$ 16 (this evaluation), and $r_0(^{190}\text{Pb})=1.511$ 6 and $r_0(^{194}\text{Po})=1.551$ 10 ([1998Ak04](#)).

[‡] For absolute intensity per 100 decays, multiply by 0.94 5.